

In the Title:

Amend the Title, as it appears on the first page and immediately above the Abstract, to read as follows:

Structure For Scalable, Low-Cost Polysilicon DRAM in a Planar Capacitor

In the Claims:

✓
Cancel claims 11-20.

- SUB
B17
A1
1. (Amended) A structure formed on a semiconductor substrate comprising:
a plurality of isolation filled trenches in the substrate;
a plurality of holes in the substrate, each having a plurality of sidewalls and a bottom wall, located in a region of the semiconductor substrate in which said plurality of isolation filled trenches are absent, said holes having a depth proximate that of said plurality of isolation filled trenches; insulating material present in each of said plurality of holes on said plurality of sidewalls and bottom wall; and
a conductor overfilling each of said holes and extending onto an adjacent upper surface of the substrate.

Remarks

Applicants respectfully request that this amendment be entered, and that their subject U.S. Patent application be passed to issuance in view thereof. The foregoing amendments are further indicated in blackline form in Exhibit A, "VERSION WITH MARKINGS TO SHOW CHANGES MADE."

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